Notice of References Cited	Application/Control No. 10/666,031	Applicant(s)/Patent Under Reexamination AIPPERSPACH ET AL.	
	Examiner Shelly A. Chase	Art Unit 2133	Page 1 of 1

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	B	US-			
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	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

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NON-PATENT DOCUMENTS

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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
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